



## Pin Description and Pin Characteristic Tables

**Table 1. Pin Descriptions**

| Number   | Name                 | Type   |          | Description                                                                                                                                                                             |
|----------|----------------------|--------|----------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 1, 9, 13 | GND                  | Power  |          | Power supply ground.                                                                                                                                                                    |
| 2        | CLK_EN               | Input  | Pullup   | Synchronizing clock enable. When HIGH, clock outputs follows clock input. When LOW, Q outputs are forced low, $\overline{Q}$ outputs are forced high. LVCMOS / LVTTTL interface levels. |
| 3        | CLK_SEL              | Input  | Pulldown | Clock select input. When HIGH, selects CLK2 input. When LOW, selects CLK1 input. LVCMOS / LVTTTL interface levels.                                                                      |
| 4        | CLK1                 | Input  | Pulldown | Single-ended clock input. LVCMOS/LVTTTL interface levels.                                                                                                                               |
| 5, 7     | nc                   | Unused |          | No connect.                                                                                                                                                                             |
| 6        | CLK2                 | Input  | Pulldown | Single-ended clock input. LVCMOS/LVTTTL interface levels.                                                                                                                               |
| 8        | OE                   | Input  | Pullup   | Output enable. Controls enabling and disabling of outputs Q0/ $\overline{Q0}$ through Q3/ $\overline{Q3}$ . LVCMOS/LVTTTL interface levels.                                             |
| 10, 18   | V <sub>DD</sub>      | Power  |          | Positive supply pins.                                                                                                                                                                   |
| 11, 12   | $\overline{Q3}$ , Q3 | Output |          | Differential output pair. LVDS interface levels.                                                                                                                                        |
| 14, 15   | $\overline{Q2}$ , Q2 | Output |          | Differential output pair. LVDS interface levels.                                                                                                                                        |
| 16, 17   | $\overline{Q1}$ , Q1 | Output |          | Differential output pair. LVDS interface levels.                                                                                                                                        |
| 19, 20   | $\overline{Q0}$ , Q0 | Output |          | Differential output pair. LVDS interface levels.                                                                                                                                        |

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

**Table 2. Pin Characteristics**

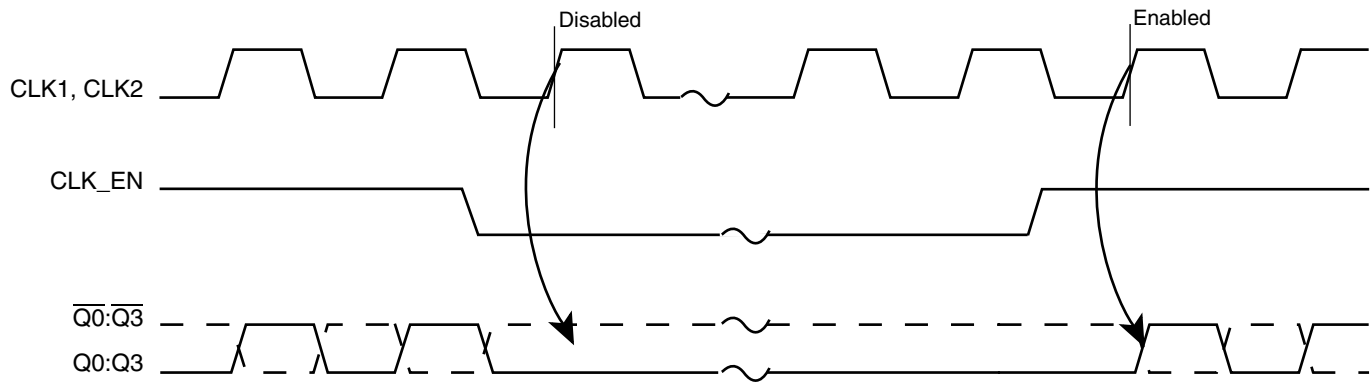
| Symbol                | Parameter               | Test Conditions | Minimum | Typical | Maximum | Units      |
|-----------------------|-------------------------|-----------------|---------|---------|---------|------------|
| C <sub>IN</sub>       | Input Capacitance       |                 |         | 4       |         | pF         |
| R <sub>PULLUP</sub>   | Input Pullup Resistor   |                 |         | 51      |         | k $\Omega$ |
| R <sub>PULLDOWN</sub> | Input Pulldown Resistor |                 |         | 51      |         | k $\Omega$ |

## Function Tables

**Table 3A. Control Input Function Table**

| Inputs |        |         |                 | Outputs |                    |
|--------|--------|---------|-----------------|---------|--------------------|
| OE     | CLK_EN | CLK_SEL | Selected Source | Q0:Q3   | $\overline{Q0:Q3}$ |
| 0      | X      | X       |                 | Hi-Z    | Hi-Z               |
| 1      | 0      | 0       | CLK1            | Low     | High               |
| 1      | 0      | 1       | CLK2            | Low     | High               |
| 1      | 1      | 0       | CLK1            | Active  | Active             |
| 1      | 1      | 1       | CLK2            | Active  | Active             |

After CLK\_EN switches, the clock outputs are disabled or enabled following a rising and falling input clock edge as shown in Figure 1. In the active mode, the state of the outputs are a function of the CLK1 and CLK2 inputs as described in Table 3B.



**Figure 1. CLK\_EN Timing Diagram**

**Table 3B. Clock Input Function Table**

| Inputs       | Outputs |                    |
|--------------|---------|--------------------|
| CLK1 or CLK2 | Q0:Q3   | $\overline{Q0:Q3}$ |
| 0            | LOW     | HIGH               |
| 1            | HIGH    | LOW                |

## Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item                                                  | Rating                   |
|-------------------------------------------------------|--------------------------|
| Supply Voltage, $V_{DD}$                              | 4.6V                     |
| Inputs, $V_I$                                         | -0.5V to $V_{DD} + 0.5V$ |
| Outputs, $I_O$<br>Continuous Current<br>Surge Current | 10mA<br>15mA             |
| Package Thermal Impedance, $\theta_{JA}$              | 73.2°C/W (0 lfpm)        |
| Storage Temperature, $T_{STG}$                        | -65°C to 150°C           |

## DC Electrical Characteristics

**Table 4A. Power Supply DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

| Symbol   | Parameter               | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|-------------------------|-----------------|---------|---------|---------|-------|
| $V_{DD}$ | Positive Supply Voltage |                 | 3.135   | 3.3     | 3.465   | V     |
| $I_{DD}$ | Power Supply Current    |                 |         |         | 52      | mA    |

**Table 4B. LVCMOS/LVTTL DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

| Symbol   | Parameter          | Test Conditions     | Minimum                        | Typical | Maximum        | Units   |
|----------|--------------------|---------------------|--------------------------------|---------|----------------|---------|
| $V_{IH}$ | Input High Voltage |                     | 2                              |         | $V_{DD} + 0.3$ | V       |
| $V_{IL}$ | Input Low Voltage  | CLK1, CLK2          | -0.3                           |         | 1.3            | V       |
|          |                    | OE, CLK_EN, CLK_SEL | -0.3                           |         | 0.8            | V       |
| $I_{IH}$ | Input High Current | CLK1, CLK2, CLK_SEL | $V_{DD} = V_{IN} = 3.465V$     |         | 150            | $\mu A$ |
|          |                    | OE, CLK_EN          | $V_{DD} = V_{IN} = 3.465V$     |         | 5              | $\mu A$ |
| $I_{IL}$ | Input Low Current  | CLK1, CLK2, CLK_SEL | $V_{DD} = 3.465V, V_{IN} = 0V$ | -5      |                | $\mu A$ |
|          |                    | OE, CLK_EN          | $V_{DD} = 3.465V, V_{IN} = 0V$ | -150    |                | $\mu A$ |

**Table 4C. LVDS DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

| Symbol          | Parameter                                 | Test Conditions | Minimum | Typical | Maximum | Units   |
|-----------------|-------------------------------------------|-----------------|---------|---------|---------|---------|
| $V_{OD}$        | Differential Output Voltage               |                 | 200     | 280     | 360     | mV      |
| $\Delta V_{OD}$ | $V_{OD}$ Magnitude Change                 |                 |         |         | 40      | mV      |
| $V_{OS}$        | Offset Voltage                            |                 | 1.125   | 1.25    | 1.375   | V       |
| $\Delta V_{OS}$ | $V_{OS}$ Magnitude Change                 |                 |         | 5       | 25      | mV      |
| $I_{OZ}$        | High Impedance Leakage                    |                 | -10     | $\pm 1$ | +10     | $\mu A$ |
| $I_{OFF}$       | Power Off Leakage                         |                 | -20     | $\pm 1$ | +20     | $\mu A$ |
| $I_{OSD}$       | Differential Output Short Circuit Current |                 |         | -3.5    | -5      | mA      |
| $I_{OS}$        | Output Short Circuit Current              |                 |         | -3.5    | -5      | mA      |
| $V_{OH}$        | Output Voltage High                       |                 |         | 1.34    | 1.6     | V       |
| $V_{OL}$        | Output Voltage Low                        |                 | 0.9     | 1.06    |         | V       |

## AC Electrical Characteristics

**Table 5. AC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

| Symbol       | Parameter                                                                 | Test Conditions                             | Minimum | Typical | Maximum | Units |
|--------------|---------------------------------------------------------------------------|---------------------------------------------|---------|---------|---------|-------|
| $f_{MAX}$    | Output Frequency                                                          |                                             |         |         | 650     | MHz   |
| $t_{PD}$     | Propagation Delay; NOTE 1                                                 | $f \leq 650MHz$                             | 1.4     |         | 3.6     | ns    |
| $\eta_{jit}$ | Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section | 156.25MHz, Integration Range: 12kHz – 20MHz |         | 0.13    |         | ps    |
| $t_{sk(o)}$  | Output Skew; NOTE 2, 4                                                    |                                             |         |         | 40      | ps    |
| $t_{sk(pp)}$ | Part-to-Part Skew; NOTE 3, 4                                              |                                             |         |         | 500     | ps    |
| $t_R / t_F$  | Output Rise/Fall Time                                                     | 20% to 80% @ 50MHz                          | 200     | 400     | 700     | ps    |
| odc          | Output Duty Cycle                                                         | $f \leq 266MHz$                             | 45      |         | 55      | %     |
|              |                                                                           | $f > 266MHz$                                | 40      |         | 60      | %     |

All parameters measured at  $f \leq 650MHz$  unless noted otherwise.

NOTE 1: Measured from  $V_{DD}/2$  of the input to the differential output crossing point.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions.

Measured at  $V_{DD}/2$  of the input to the differential output crossing point.

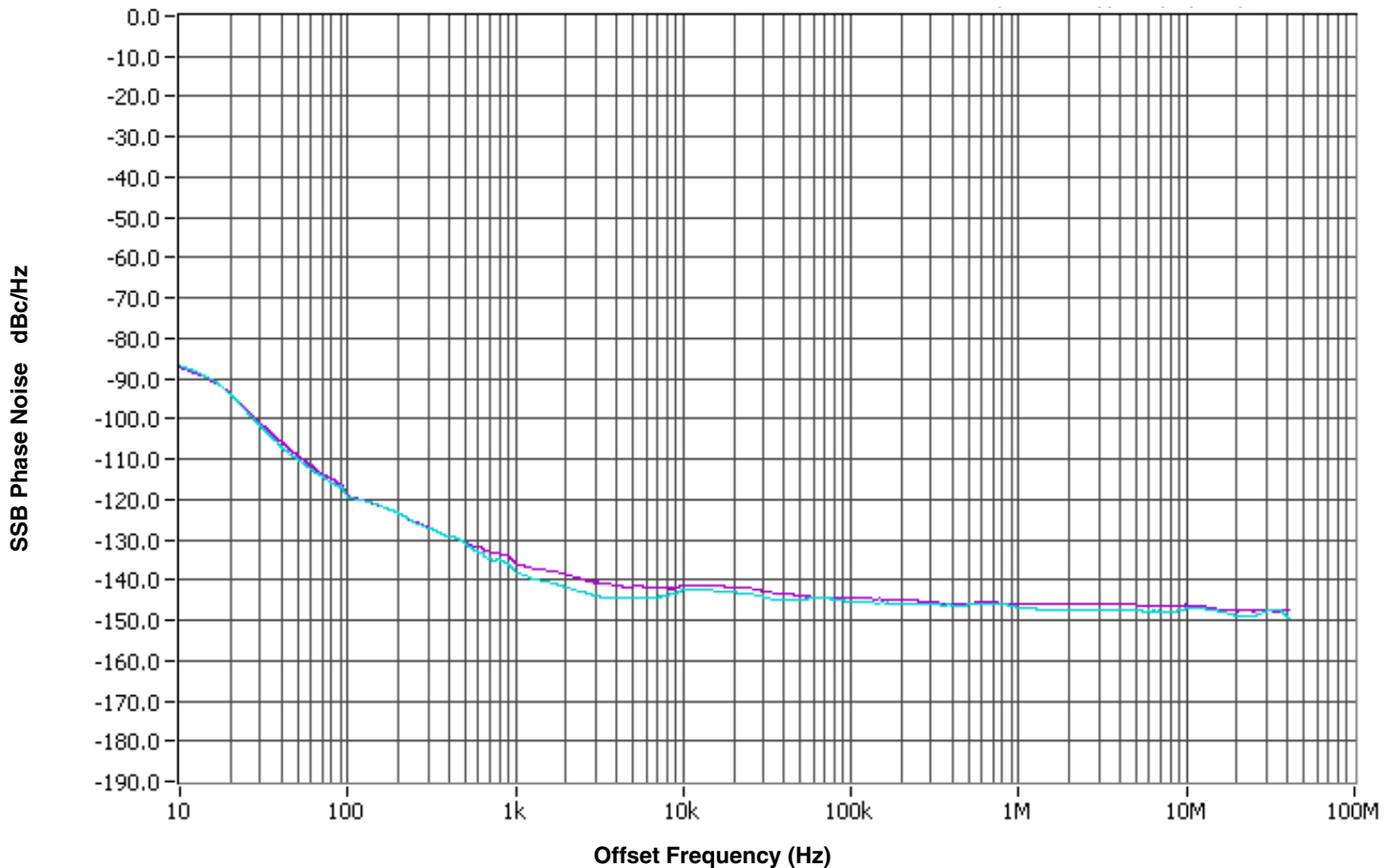
NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

## Additive Phase Jitter

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the **dBc Phase Noise**. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio

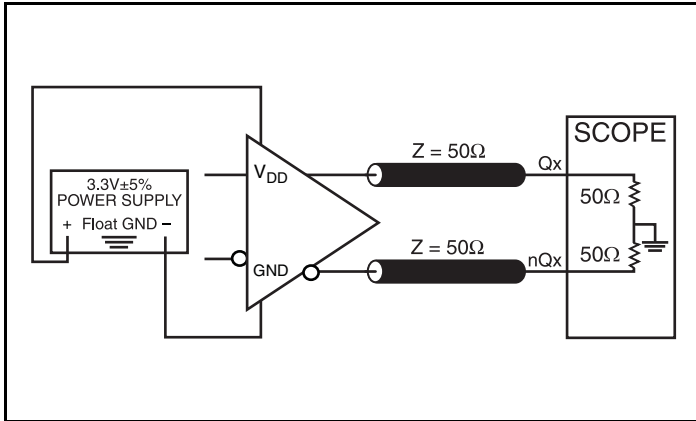
of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a **dBc** value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.



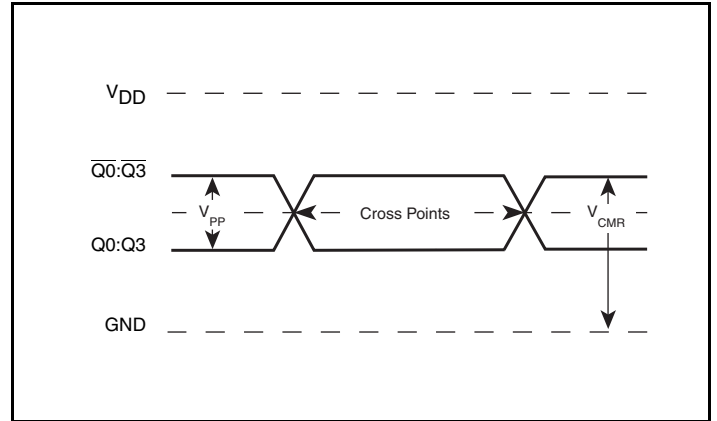
As with most timing specifications, phase noise measurements have issues. The primary issue relates to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor

of the device. This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependent on the input source and measurement equipment.

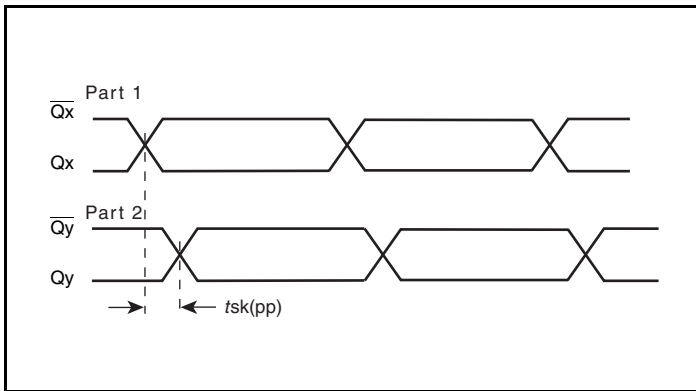
## Parameter Measurement Information



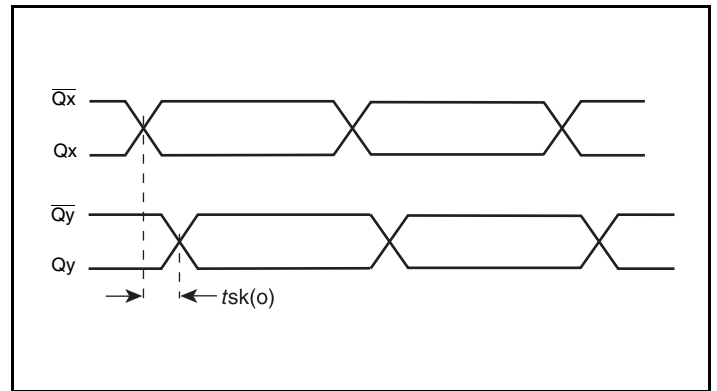
3.3V LVDS Output Load AC Test Circuit



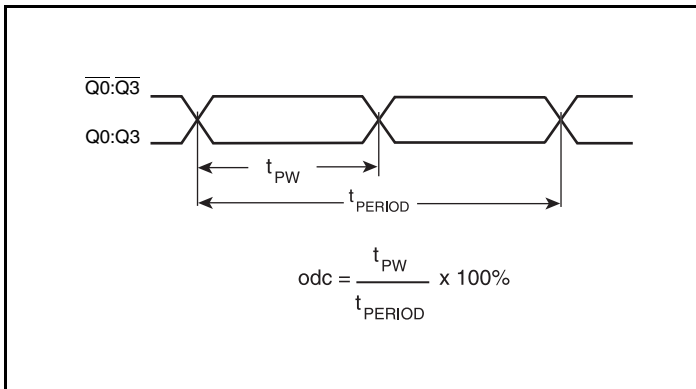
Differential Output Level



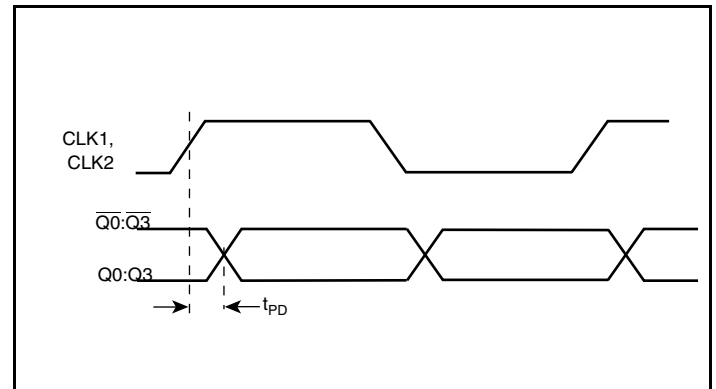
Part-to-Part Skew



Output Skew

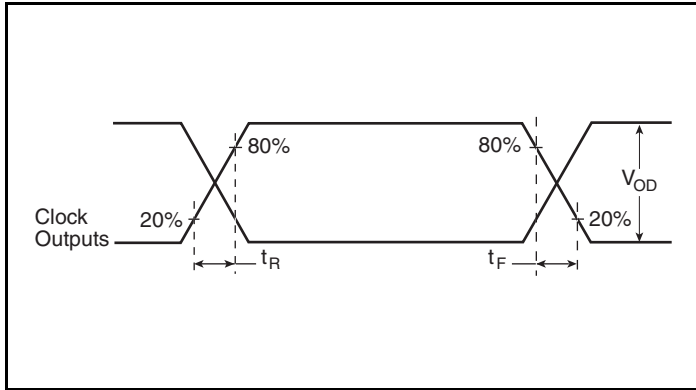


Output Duty Cycle/Pulse Width/Period

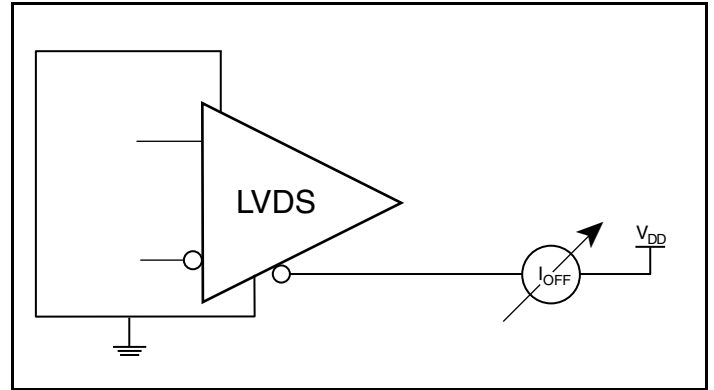


Propagation Delay

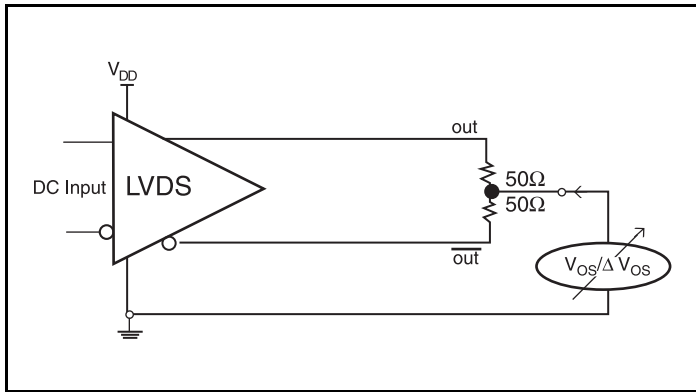
## Parameter Measurement Information, continued



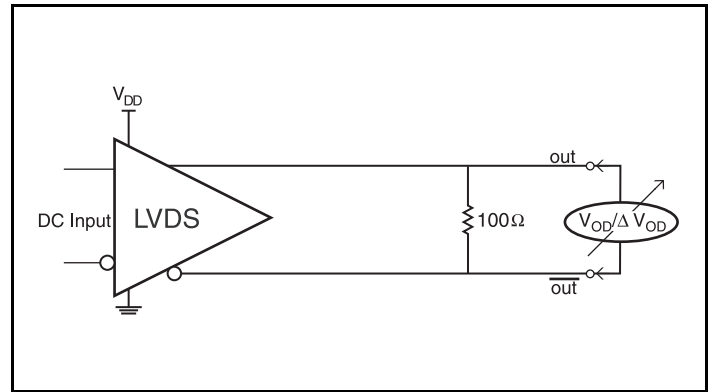
**Output Rise/Fall Time**



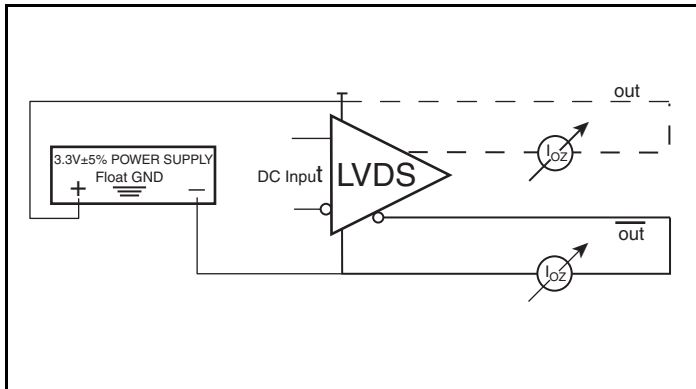
**Power Off Leakage Setup**



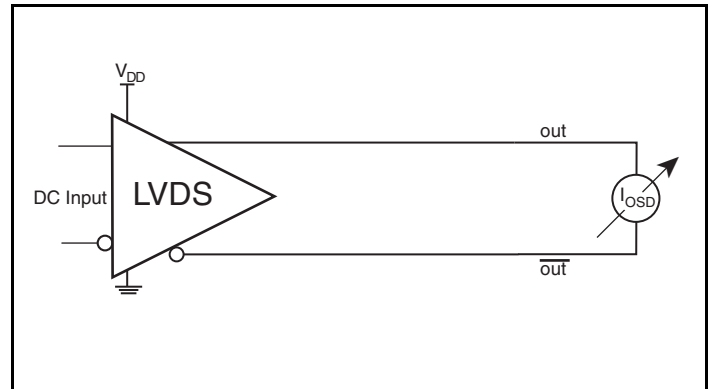
**Offset Voltage Setup**



**Differential Output Voltage Setup**

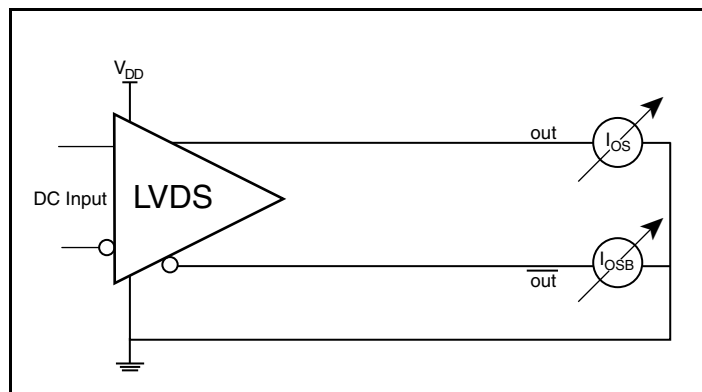


**High Impedance Leakage Current Setup**



**Differential Output Short Circuit Setup**

## Parameter Measurement Information, continued



**Output Short Circuit Current Setup**

## Applications Information

### Recommendations for Unused Input and Output Pins

#### Inputs:

##### CLK Inputs

For applications not requiring the use of a clock input, it can be left floating. Though not required, but for additional protection, a 1k $\Omega$  resistor can be tied from the CLK input to ground.

##### LVC MOS Control Pins

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A 1k $\Omega$  resistor can be used.

#### Outputs:

##### LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100 $\Omega$  across. If they are left floating, there should be no trace attached.

### LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance ( $Z_T$ ) is between 90 $\Omega$  and 132 $\Omega$ . The actual value should be selected to match the differential impedance ( $Z_0$ ) of your transmission line. A typical point-to-point LVDS design uses a 100 $\Omega$  parallel resistor at the receiver and a 100 $\Omega$  differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The

standard termination schematic as shown in Figure 2 can be used with either type of output structure. Figure 3, which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF. If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.

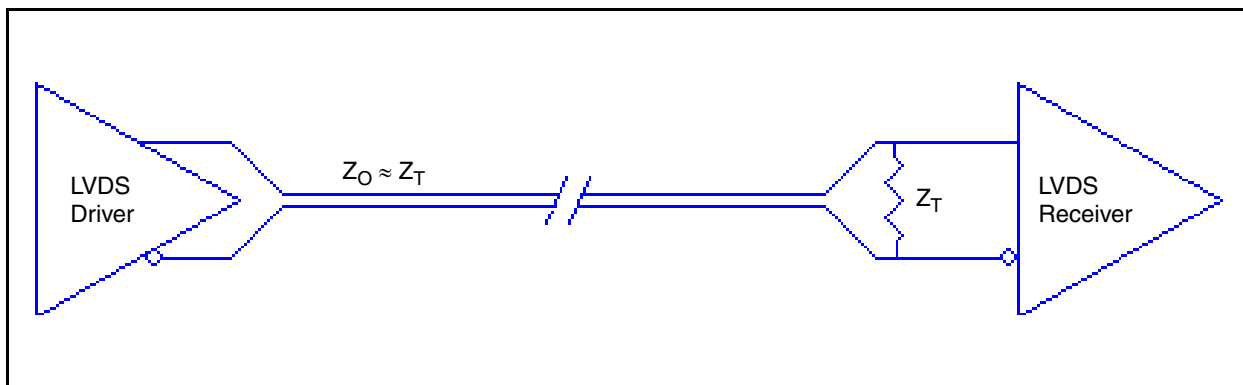


Figure 2. Standard LVDS Termination

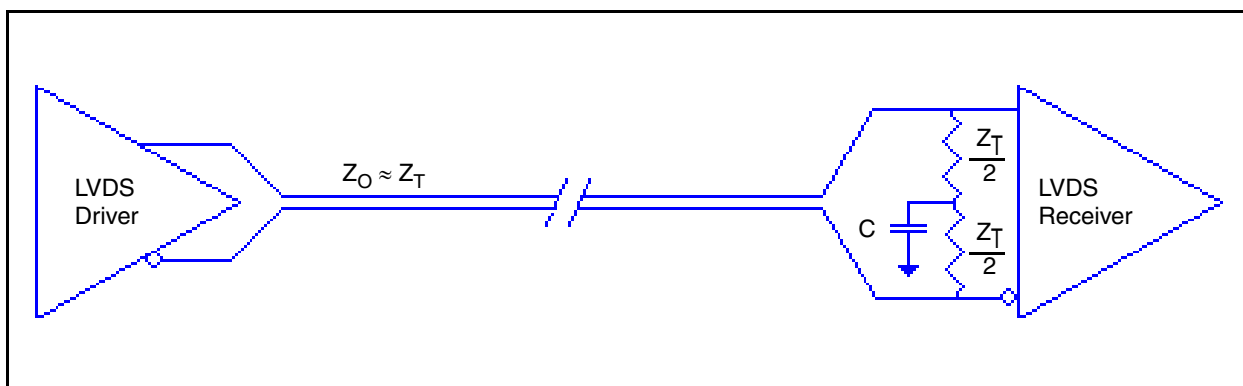


Figure 3. Optional LVDS Termination

## Power Considerations

This section provides information on power dissipation and junction temperature for the 8545. Equations and example calculations are also provided.

### 1. Power Dissipation.

The total power dissipation for the 8545 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for  $V_{DD} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)<sub>MAX</sub> =  $V_{DD\_MAX} * I_{DD\_MAX} = 3.465V * 52mA = \mathbf{180.18mW}$

### 2. Junction Temperature.

Junction temperature,  $T_j$ , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature,  $T_j$ , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for  $T_j$  is as follows:  $T_j = \theta_{JA} * Pd_{total} + T_A$

$T_j$  = Junction Temperature

$\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

$Pd_{total}$  = Total Device Power Dissipation (example calculation is in section 1 above)

$T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming a moderate air flow of 200 linear feet per minute and a multi-layer board, the appropriate value is 66.6°C/W per Table 6 below.

Therefore,  $T_j$  for an ambient temperature of 85°C with all outputs switching is:

$85^\circ C + 0.180W * 66.6^\circ C/W = 97^\circ C$ . This is well below the limit of 125°C.

This calculation is only an example.  $T_j$  will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (single layer or multi-layer).

**Table 6. Thermal Resistance  $\theta_{JA}$  for 20 Lead TSSOP, Forced Convection**

| Linear Feet per Minute                       | $\theta_{JA}$ by Velocity |          |          |
|----------------------------------------------|---------------------------|----------|----------|
|                                              | 0                         | 200      | 500      |
| Single-Layer PCB, JEDEC Standard Test Boards | 114.5°C/W                 | 98.0°C/W | 88.0°C/W |
| Multi-Layer PCB, JEDEC Standard Test Boards  | 73.2°C/W                  | 66.6°C/W | 63.5°C/W |

## Reliability Information

Table 7.  $\theta_{JA}$  vs. Air Flow Table for a 20 Lead TSSOP

| $\theta_{JA}$ by Velocity                    |           |          |          |
|----------------------------------------------|-----------|----------|----------|
| Linear Feet per Minute                       | 0         | 200      | 500      |
| Single-Layer PCB, JEDEC Standard Test Boards | 114.5°C/W | 98.0°C/W | 88.0°C/W |
| Multi-Layer PCB, JEDEC Standard Test Boards  | 73.2°C/W  | 66.6°C/W | 63.5°C/W |

## Transistor Count

The transistor count for 8545 is: 644

## Package Outline and Package Dimensions

Package Outline - G Suffix for 20 Lead TSSOP

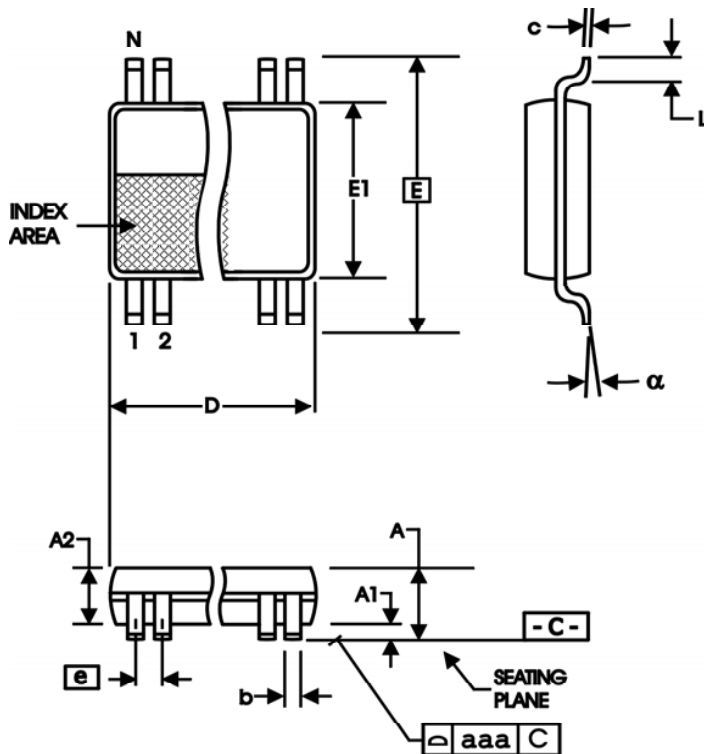


Table 8. Package Dimensions

| All Dimensions in Millimeters |            |         |
|-------------------------------|------------|---------|
| Symbol                        | Minimum    | Maximum |
| N                             | 20         |         |
| A                             |            | 1.20    |
| A1                            | 0.05       | 0.15    |
| A2                            | 0.80       | 1.05    |
| b                             | 0.19       | 0.30    |
| c                             | 0.09       | 0.20    |
| D                             | 6.40       | 6.60    |
| E                             | 6.40 Basic |         |
| E1                            | 4.30       | 4.50    |
| e                             | 0.65 Basic |         |
| L                             | 0.45       | 0.75    |
| $\alpha$                      | 0°         | 8°      |
| aaa                           |            | 0.10    |

Reference Document: JEDEC Publication 95, MO-153

## Ordering Information

Table 9. Ordering Information

| Part/Order Number | Marking      | Package                  | Shipping Packaging | Temperature   |
|-------------------|--------------|--------------------------|--------------------|---------------|
| ICS8545BGILF      | ICS8545BGILF | 20 Lead TSSOP, Lead-Free | Tube               | -40°C to 85°C |
| ICS8545BGILFT     | ICS8545BGILF | 20 Lead TSSOP, Lead-Free | Tape & Reel        | -40°C to 85°C |

## Revision History Sheet

| Rev | Table | Page | Description of Change                                          | Date     |
|-----|-------|------|----------------------------------------------------------------|----------|
| B   | T5    | 1    | Features Section - added Additive Phase Jitter bullet.         | 5/31/07  |
|     |       | 5    | AC Characteristics Table - added Additive Phase Jitter spec.   |          |
|     |       | 6    | Added <i>Additive Phase Jitter Plot</i> .                      |          |
|     |       | 11   | Added <i>Power Considerations</i> section.                     |          |
| B   | T9    | 13   | Ordering Information Table - added lead-free marking.          | 2/15/08  |
| B   | T9    | 13   | Removed leaded orderable parts from Ordering Information table | 11/15/12 |
| C   |       | 10   | Updated LVDS Driver Termination application note.              | 12/8/15  |
|     |       |      | Deleted HiperClocks references throughout the datasheet.       |          |
|     |       |      | Updated header/footer.                                         |          |
|     |       |      | Deleted "ICS" prefix and "I" suffix from part number.          |          |

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